

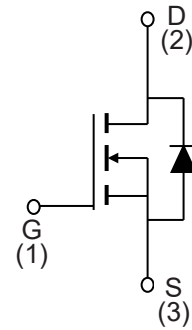
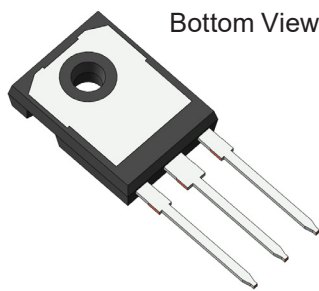
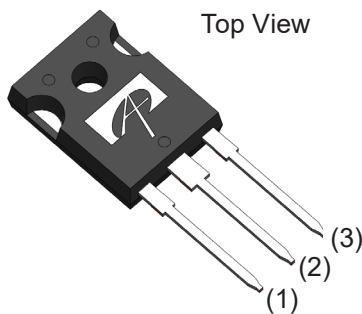
Features

- Proprietary α SiC MOSFET technology
- Low loss, with low $R_{DS(ON)}$
- Fast switching with low R_G and low capacitance
- Optimized gate drive voltage ($V_{GS} = 15V$)
- Low reverse recovery diode (Q_{rr})
- AEC-Q101 Automotive Qualified

Applications

- xEV Charger
- Electric Vehicle Supply Equipment (EVSE)
- Motor Drives
- Automotive Inverters

Pin Configuration



Product Summary

$V_{DS} @ T_{J, max}$	1200V
I_{DM}	85A
$R_{DS(ON), typ}$	65m Ω
Q_{rr}	155nC
$E_{OSS} @ 800V$	30 μ J
100 % UIS Tested	

Ordering Part Number	Package Type	Form	Shipping Quantity
AOK065V120X2Q	TO-247-3L	Tube	30/Tube

Absolute Maximum Ratings

($T_A = 25^\circ C$, unless otherwise noted)

Symbol	Parameter	AOK065V120X2Q	Units
V_{DS}	Drain-Source Voltage	1200	V
$V_{GS, MAX}$	Gate-Source Voltage	Maximum	-8/+18
$V_{GS, OP, TRANS}$		Max Transient ^(A)	-8/+20
$V_{GS, OP}$		Recommended Operating ^(B)	-5/+15
I_D	Continuous Drain Current	$T_C = 25^\circ C$	40.3
		$T_C = 100^\circ C$	29.6
I_{DM}	Pulsed Drain Current ^(C)	85	A
E_{AS}	Single Pulsed Avalanche Energy ^(D)	250	mJ
P_D	Power Dissipation ^(C)	187.5	W
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to 175	$^\circ C$
T_L	Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds	300	$^\circ C$

Thermal Characteristics

Symbol	Parameter	AOK065V120X2Q	Units
R _{θJA}	Maximum Junction-to-Ambient ^(E,F)	40	°C/W
R _{θJC}	Maximum Junction-to-Case ^(G)	0.8	°C/W

Electrical Characteristics

(T_A = 25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units	
STATIC							
V _{(BR)DSS}	Drain-Source Breakdown Voltage	I _D =250 μA, V _{GS} =0V, T _J =25°C	1200			V	
		I _D =250 μA, V _{GS} =0V, T _J =150°C	1200			V	
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =1200V, V _{GS} =0V			50	μA	
I _{GSS}	Gate-Source Leakage Current	V _{DS} =0V, V _{GS} =+15/-5V			±100	nA	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =10mA	1.8	2.8	3.5	V	
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =15V, I _D =10A	T _J =25°C	65	85	mΩ	
			T _J =150°C	90		mΩ	
g _{fs}	Forward Transconductance	V _{DS} =20V, I _D =20V		12		S	
V _{SD}	Diode Forward Voltage	I _S =10A, V _{GS} =-5V		4.1	5	V	
DYNAMIC							
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =800V, f=1MHz		1716		pF	
C _{oss}	Output Capacitance			71		pF	
C _{rss}	Reverse Transfer Capacitance			5		pF	
E _{oss}	Coss Stored Energy			30		μJ	
R _G	Gate Resistance	f=1MHz		1.7		Ω	
SWITCHING							
Q _g	Total Gate Charge	V _{GS} =-5/+15V, V _{DS} =800V, I _D =20A		62.3		nC	
Q _{gs}	Gate Source Charge			23.1		nC	
Q _{gd}	Gate Drain Charge			23.7		nC	
t _{d(on)}	Turn-On Delay Time	V _{GS} =0V/+15V, V _{DS} =800V, I _D =20A, R _G =5Ω		14.6		ns	
t _r	Turn-On Rise Time			36.2		ns	
t _{d(off)}	Turn-Off Delay Time			20.8		ns	
t _f	Turn-Off Fall Time			10.2		ns	
E _{on}	Turn-On Energy		L=120 μH		325		μJ
E _{off}	Turn-Off Energy	FWD: AOK065V120X2Q		23		μJ	
E _{tot}	Total Switching Energy			348		μJ	
t _{rr}	Body Diode Reverse Recovery Time	I _F =20A, di/dt=1560A/μs, V _{DS} =800V		27		ns	
I _{rm}	Peak Reverse Recovery Current				10		A
Q _{rr}	Body Diode Reverse Recovery Charge				155		nC

Notes:

- < 1% duty cycle, f > 1 Hz
- Device can be operated at V_{GS}=0/15V. Actual operating VGS will depend on application specifics such as parasitic inductance and dV/dt but should not exceed maximum ratings.
- The power dissipation P_D is based on T_{J(MAX)}=175°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
- L=5mH, I_{AS}=10A, R_G=25Ω, Starting T_J=25°C.
- The value of R_{θJA} is measured with the device in a still air environment

- with T_A=25°C.
- The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.
- The value of R_{θJC} is measured with the device mounted to a large heat-sink, assuming a maximum junction temperature of T_{J(MAX)}=175°C.
- The static characteristics in Figures 1 to 8 are obtained using < 300ms pulses, duty cycle 0.5% max.
- These curves are based on R_{θJC} which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=175°C. The SOA curve provides a single pulse rating.

Typical Electrical and Thermal Characteristics

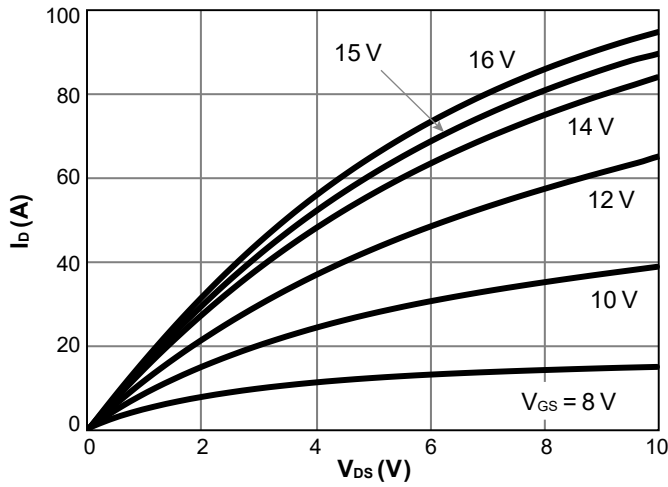


Figure 1. On-Region Characteristics $T_J = 25^\circ\text{C}$

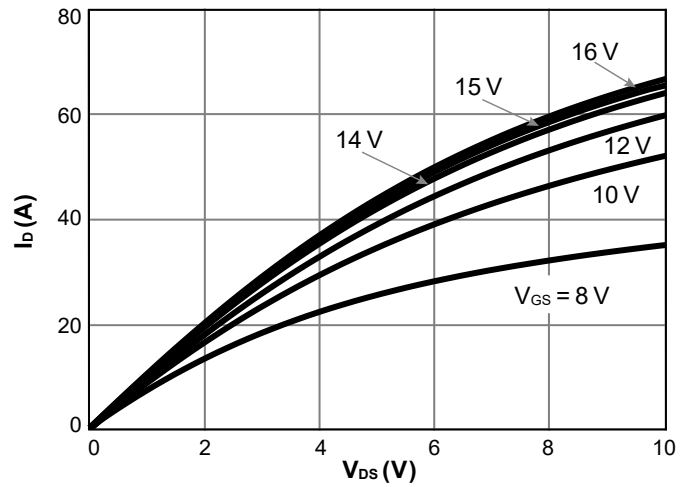


Figure 2. On-Region Characteristics $T_J = 175^\circ\text{C}$

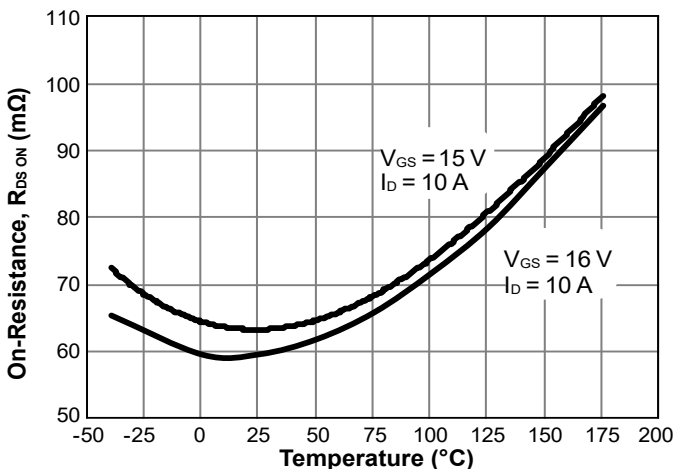


Figure 3. On-Resistance vs. Junction Temperature

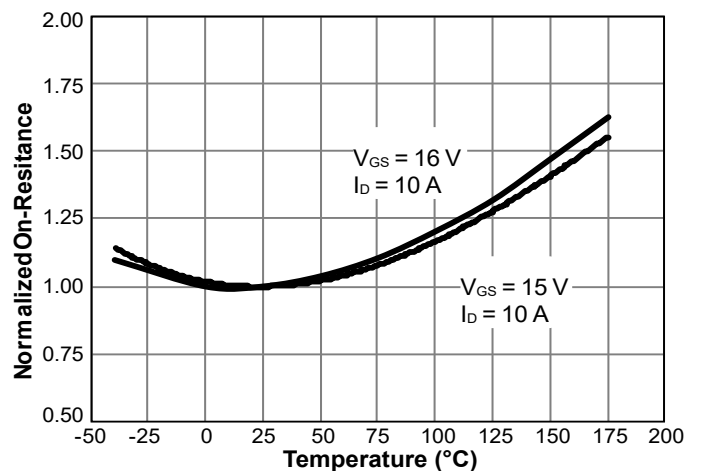


Figure 4. Normalized On-Resistance vs. Junction Temperature

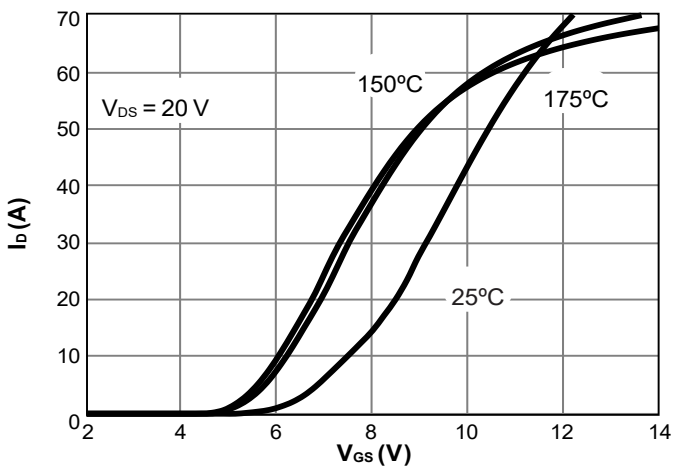


Figure 5. Transfer Characteristics

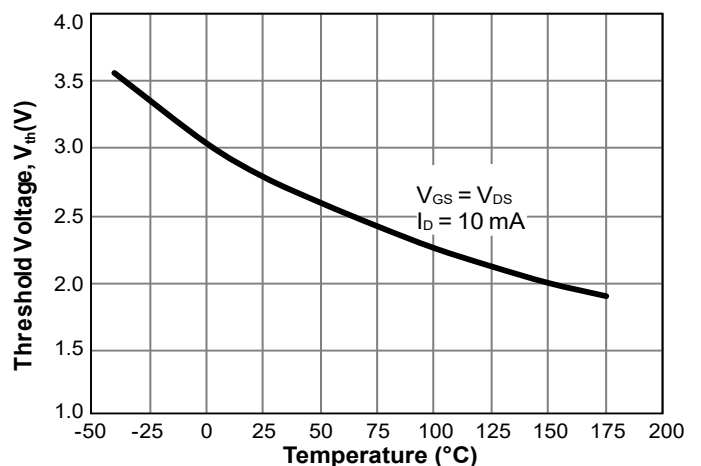


Figure 6. Threshold Voltage vs. Junction Temperature

Typical Electrical and Thermal Characteristics (Continued)

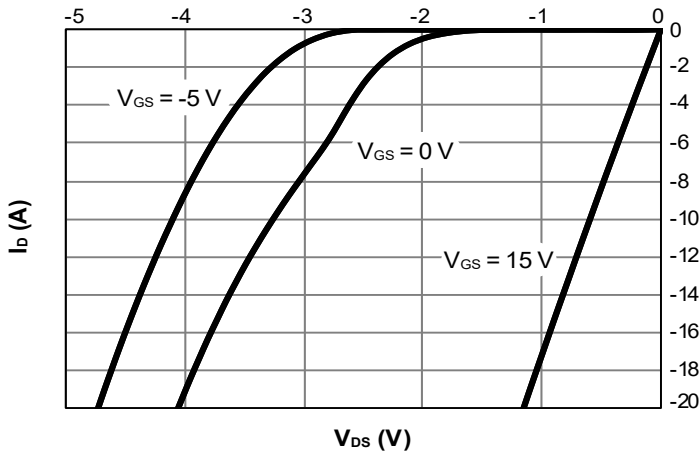


Figure 7. Body-Diode Characteristics at 25°C

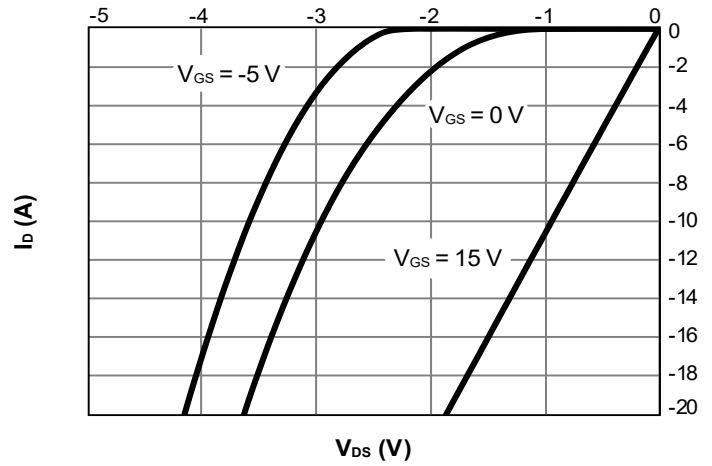


Figure 8. Body-Diode Characteristics at 175°C

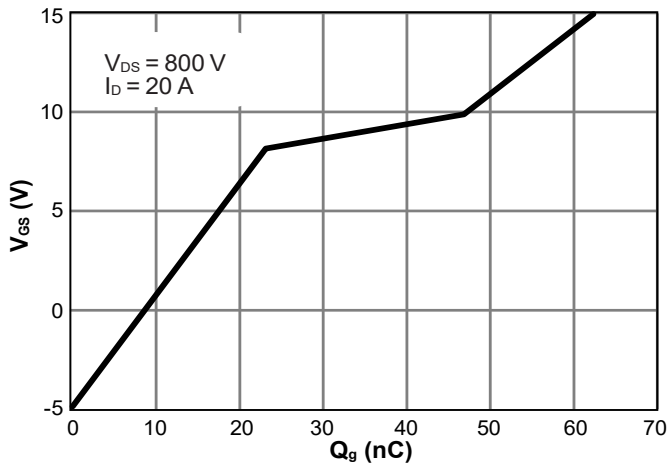


Figure 9. Gate-Charge Characteristics

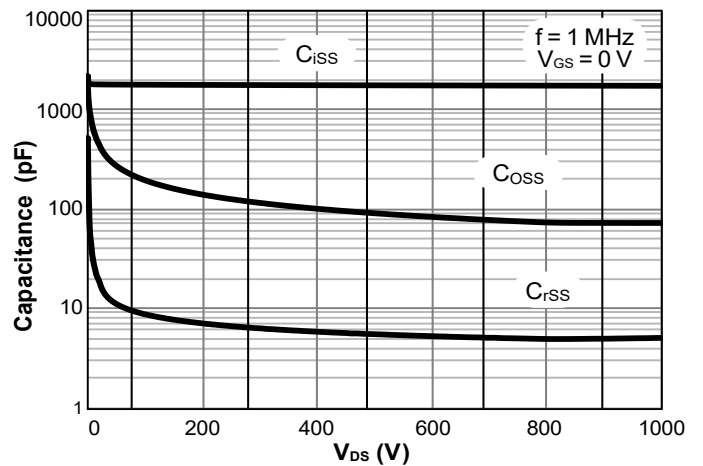


Figure 10. Capacitance Characteristics

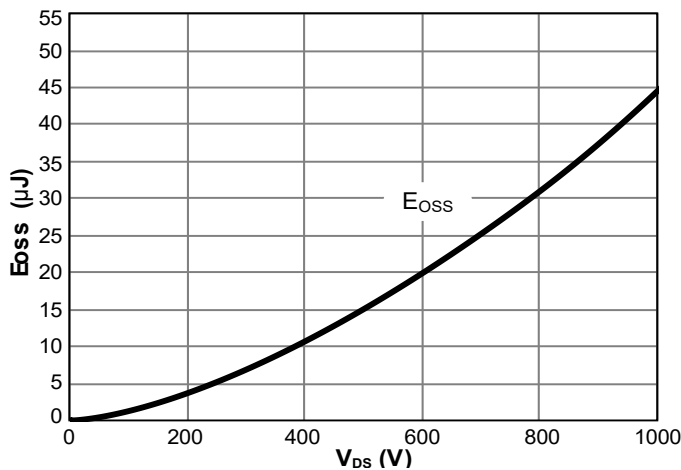


Figure 11. Coss stored Energy

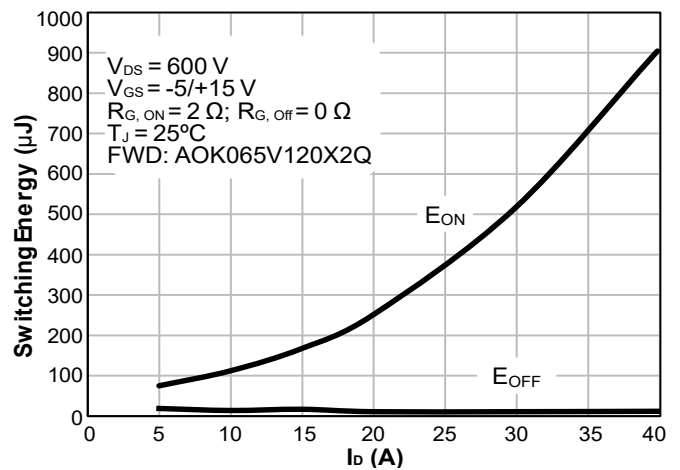


Figure 12. Switching Energy vs. Drain Current

Typical Electrical and Thermal Characteristics (Continued)

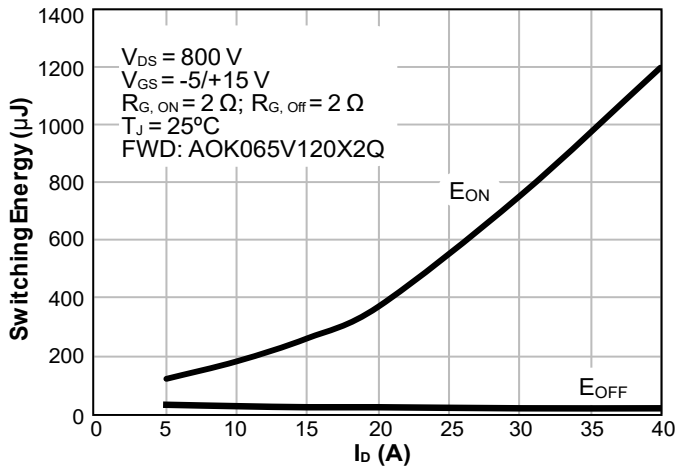


Figure 13. Switching Energy vs. Drain Current

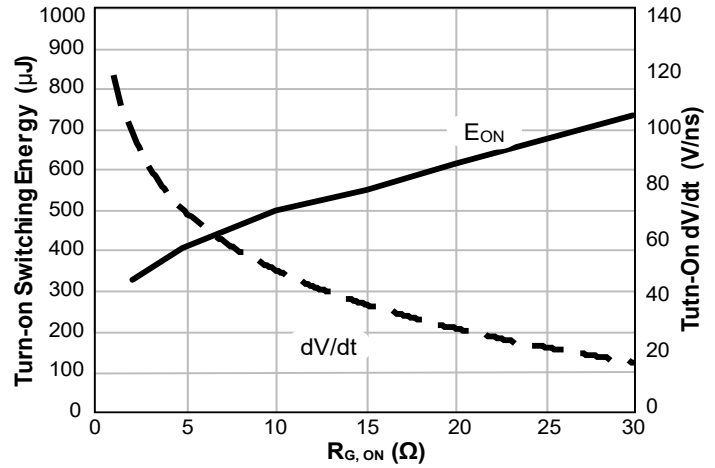


Figure 14. Turn-On Energy and dV/dt vs. External Gate Resistance

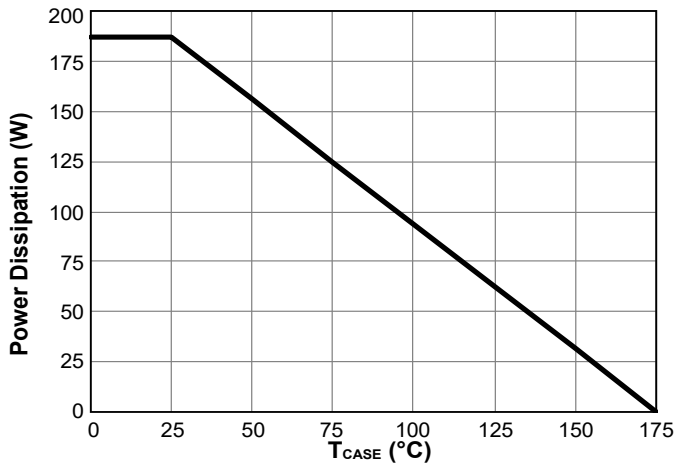


Figure 15. Power De-rating (Note I)

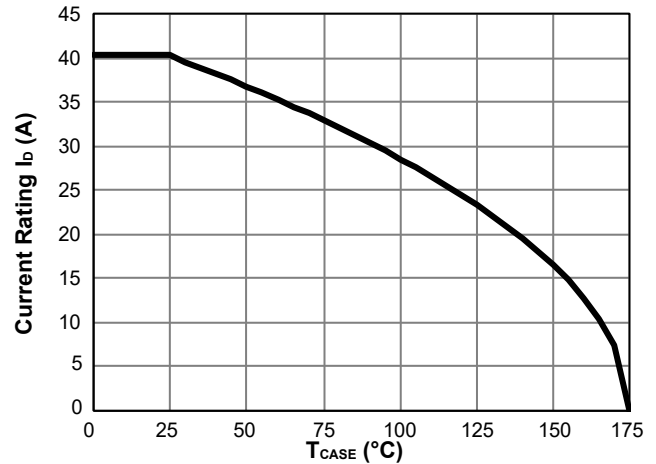


Figure 16. Current De-rating (Note I)

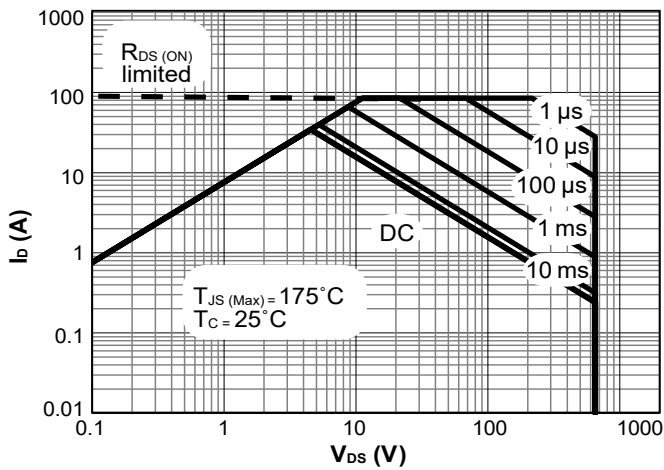


Figure 17. Maximum Forward Biased Safe Operating Area for AOK065V120X2Q (Note I)

Typical Electrical and Thermal Characteristics (Continued)

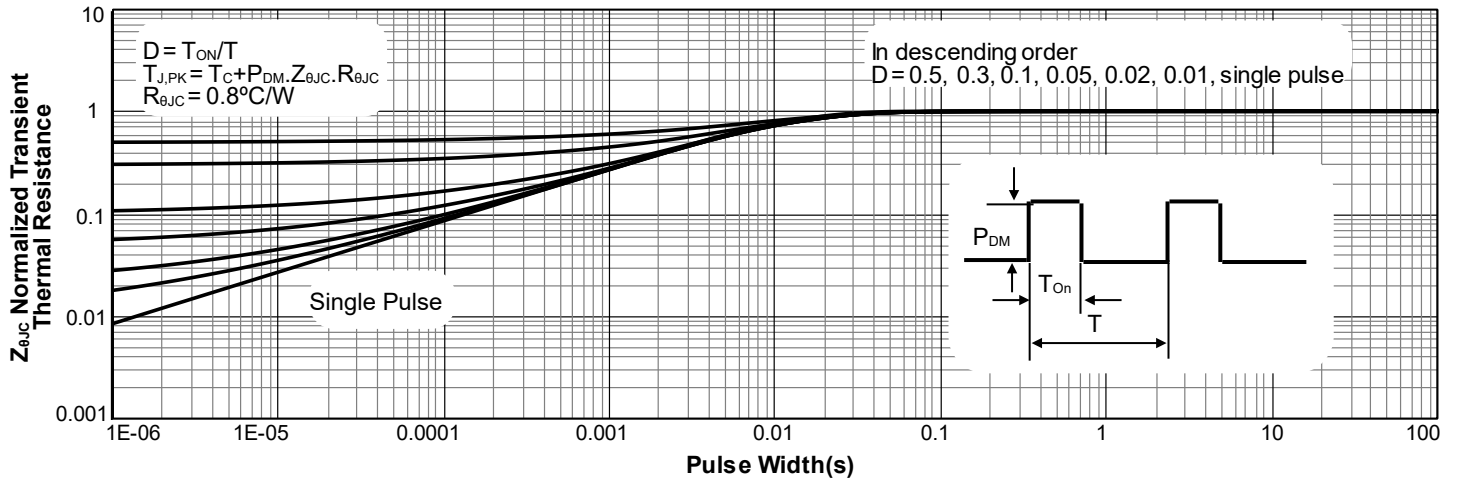


Figure 18. Normalized Maximum Transient Thermal Impedance for AOK065V120X2Q (Note I)

Test Circuits and Waveforms

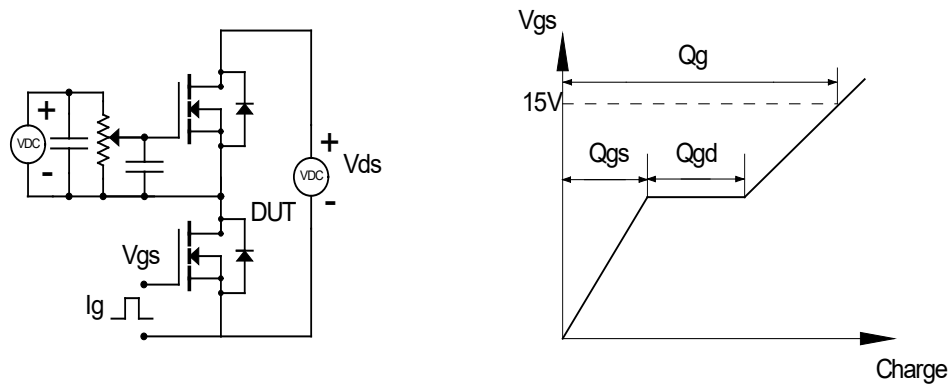


Figure 19. Gate Charge Test Circuits and Waveforms

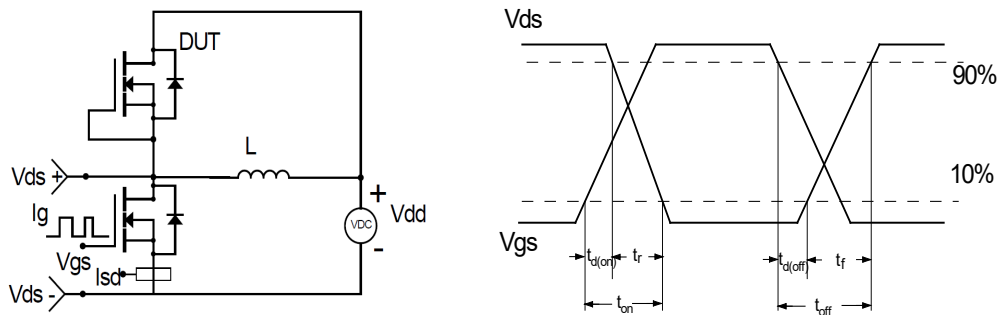


Figure 20. Inductive Switching Test Circuit and Waveforms

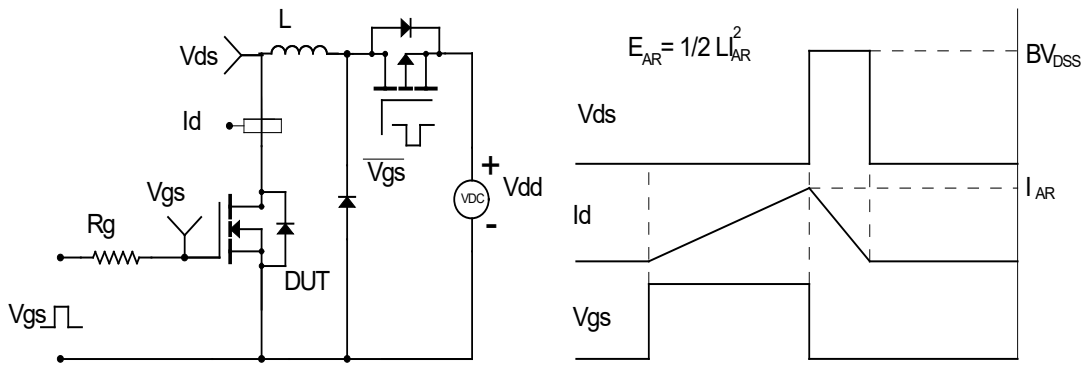


Figure 21. Unclamped Inductive Switching (UIS) Test Circuit and Waveforms

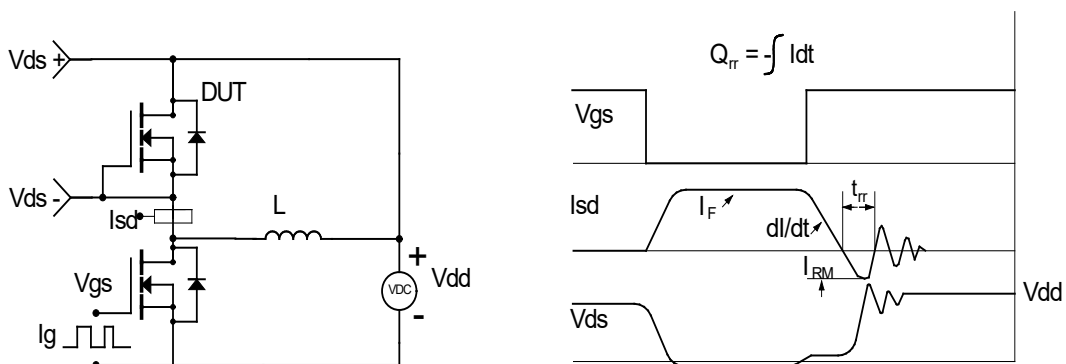
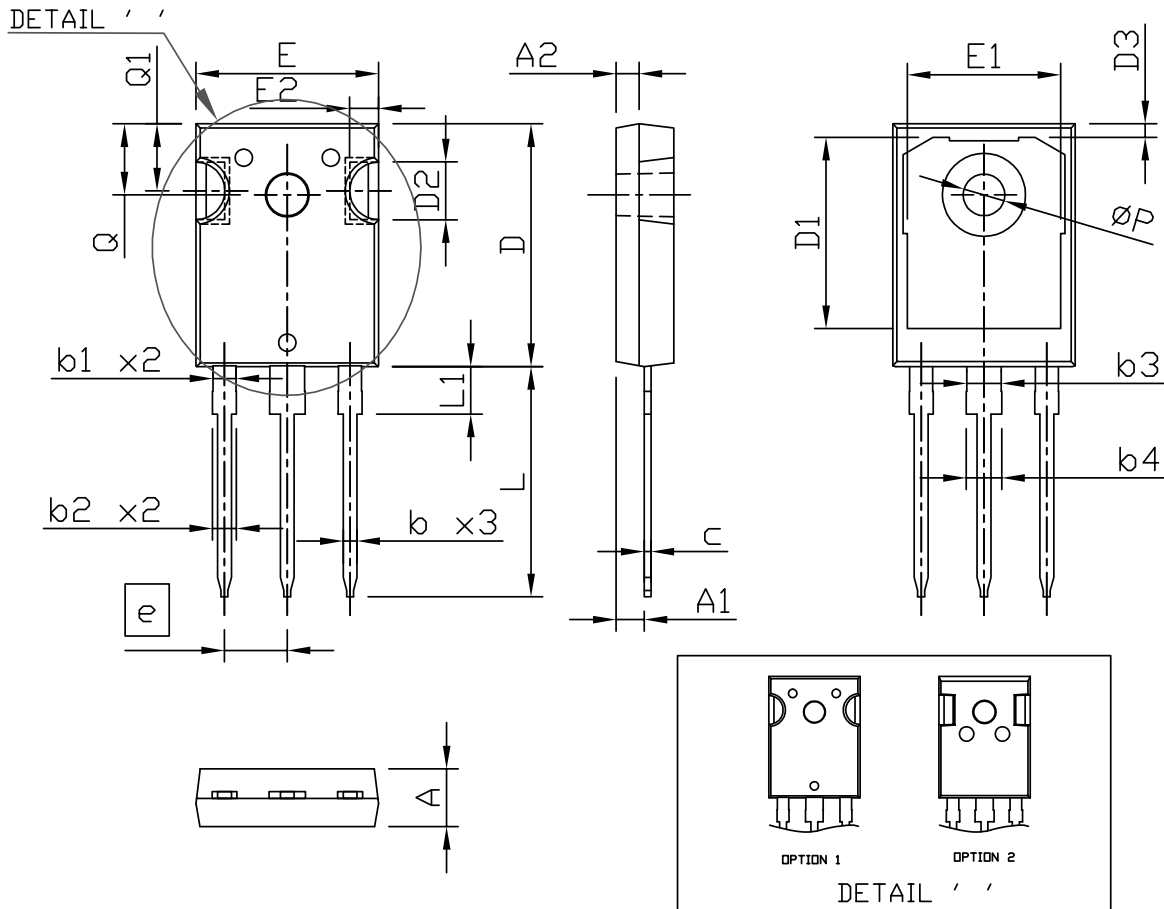
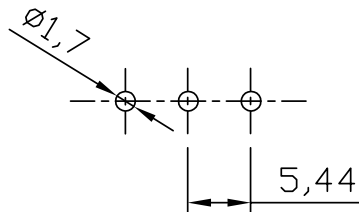


Figure 22. Diode Recovery Test Circuits and Waveforms

Package Dimensions, TO-247-3L



RECOMMENDED LAND PATTERN



UNIT: mm

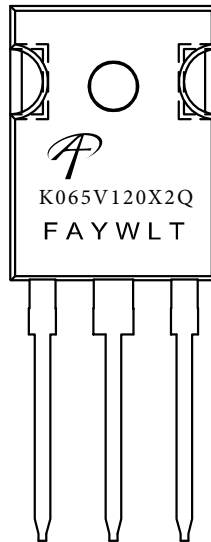
SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.90	5.00	5.10	0.193	0.197	0.201
A1	2.31	2.42	2.52	0.091	0.095	0.099
A2	1.90	2.00	2.10	0.075	0.079	0.083
b	1.16	1.22	1.27	0.046	0.048	0.050
b1	1.96	2.02	2.07	0.078	0.080	0.081
b2	2.00	2.10	2.20	0.079	0.083	0.087
b3	2.96	3.02	3.07	0.117	0.119	0.121
b4	3.00	3.10	3.20	0.118	0.122	0.126
c	0.59	0.62	0.66	0.023	0.024	0.026
D	20.90	21.00	21.10	0.823	0.827	0.831
D1	16.25	16.55	16.85	0.640	0.652	0.663
D2	5.00 TYP			0.197 TYP		
D3	1.05	1.20	1.35	0.041	0.047	0.053
e	5.44 BSC			0.214 BSC		
E	15.70	15.80	15.90	0.618	0.622	0.626
E1	13.06	13.26	13.50	0.514	0.522	0.530
E2	2.50 TYP			0.098 TYP		
L	19.72	19.92	20.12	0.776	0.784	0.792
L1	---	---	4.30	---	---	0.169
Q	6.15 BSC			0.242 BSC		
Q1	5.60	5.80	6.00	0.220	0.228	0.236
ØP	3.55	3.60	3.70	0.140	0.142	0.146

NOTE

1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 6 MILS EACH.
2. CONTROLLING DIMENSION IS MILLIMETER.
CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.

Part Marking

AOK065V120X2Q
TO-247-3L



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